TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

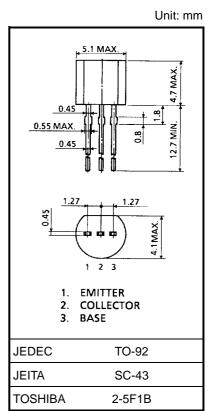
2SC3266

Power Amplifier Applications Power Switching Applications

- Low saturation voltage: $V_{CE (sat)} = 0.5 \text{ V (max) (IC} = 2 \text{ A)}$
- Complementary to 2SA1296

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	20	V	
Collector-emitter voltage	V _{CEO}	20	V	
Emitter-base voltage	V _{EBO}	6	V	
Collector current	IC	2	Α	
Base current	I _B	0.5	Α	
Collector power dissipation	PC	750	mW	
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	-55~150	°C	

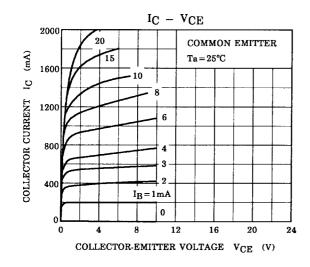


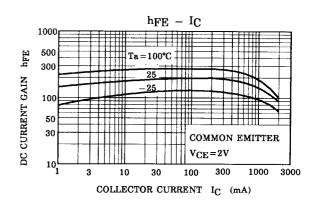
Weight: 0.21 g (typ.)

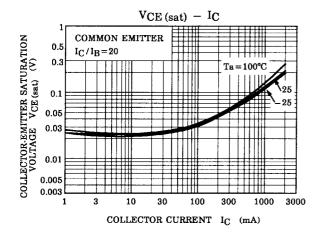
Electrical Characteristics (Ta = 25°C)

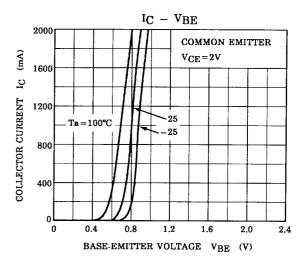
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 20 \text{ V}, I_{E} = 0$	_	_	0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 6 V, I _C = 0	_	_	0.1	μΑ
Collector-emitter breakdown voltage	V (BR) CEO	$I_C = 10 \text{ mA}, I_B = 0$	20	_	_	V
Emitter-base breakdown voltage	V (BR) EBO	I _E = 0.1 mA, I _C = 0	6	_	_	V
DC current gain	h _{FE (1)} (Note)	V _{CE} = 2 V, I _C = 0.1 A	120	_	700	
	h _{FE} (2)	V _{CE} = 2 V, I _C = 2 A	75	_	_	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = 2 A, I _B = 0.1 A	_	_	0.5	V
Base-emitter voltage	V _{BE}	V _{CE} = 2 V, I _C = 0.1 A	_	_	0.85	V
Transition frequency	f _T	V _{CE} = 2 V, I _C = 0.5 A	_	120	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	30	_	pF

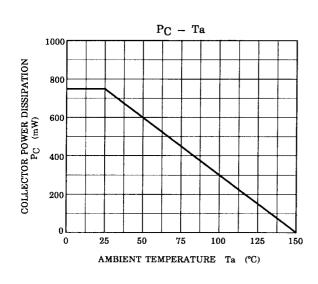
Note: hFE (1) classification Y: 120~240, GR: 200~400, BL: 350~700

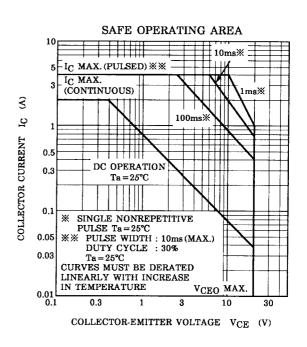












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